



Surface Mount PNP Silicon VHF-UHF Amplifier Transistors

Qualified per MIL-PRF-19500/426

Qualified Levels:
JAN, JANTX,
and JANTXV

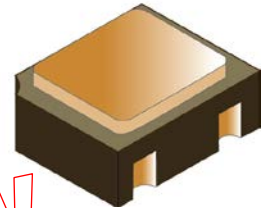
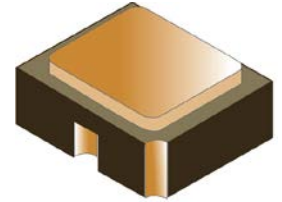
DESCRIPTION

The 2N4957UB is a military qualified silicon PNP amplifier transistor designed for VHF-UHF equipment and other high-reliability applications. Common applications include high gain low noise amplifier; oscillator, and mixer applications. It is also available in a low-profile TO-72 leaded package.

Important: For the latest information, visit our website <http://www.microsemi.com>.

FEATURES

- JEDEC registered 2N4957
- JAN, JANTX, and JANTXV military qualified versions are available per MIL-PRF-19500/426 (See [part nomenclature](#) for all available options)
- RoHS compliant



UB Package

APPLICATIONS / BENEFITS

- Low-power, ultra-high frequency transistor
- Leaded metal TO-72 package

Also available in:

 **TO-72 Package**
(leaded top hat)
[2N4957](#)

MAXIMUM RATINGS @ T_A = +25 °C

Parameters/Test Conditions	Symbol	Value	Unit
Junction and Storage Temperature	T _J and T _{STG}	-65 to +200	°C
Collector-Emitter Voltage	V _{CEO}	-30	V
Collector-Base Voltage	V _{CBO}	-30	V
Emitter-Base Voltage	V _{EBO}	-3	V
Total Power Dissipation ⁽¹⁾	P _T	200	mW
Collector Current	I _C	-30	mA

Notes: 1. Derate linearly 1.14 mW/°C for T_A > +25 °C

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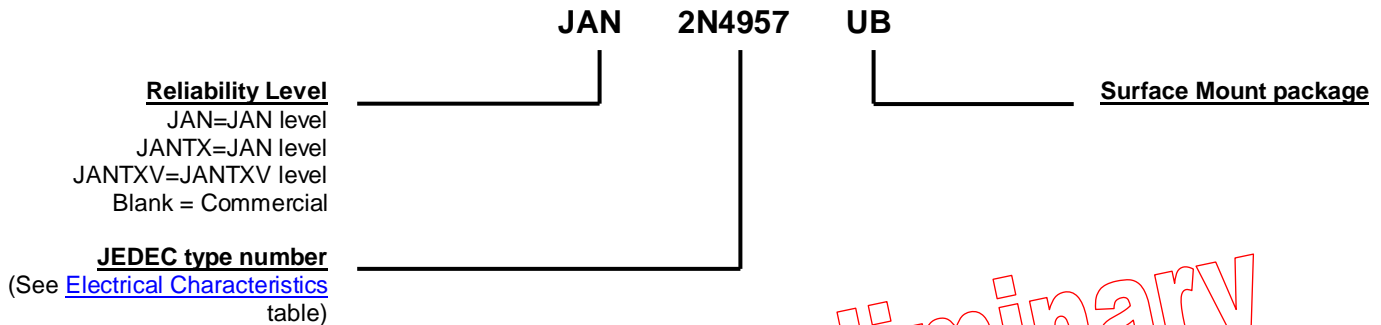
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MECHANICAL and PACKAGING

- CASE: Ceramic
- TERMINALS: Gold plating over nickel underplate
- MARKING: Part number, date code, manufacturer's ID
- POLARITY: PNP, see case outline on last page
- TAPE & REEL option: Standard per EIA-418D. Consult factory for quantities
- WEIGHT: < 0.04 grams
- See [Package Dimensions](#) on last page.

PART NOMENCLATURE

SYMBOLS & DEFINITIONS

Symbol	Definition
I_B	Base current: The value of the dc current into the base terminal.
I_C	Collector current: The value of the dc current into the collector terminal.
I_E	Emitter current: The value of the dc current into the emitter terminal.
T_A	Ambient temperature: The air temperature measured below a device, in an environment of substantially uniform temperature, cooled only by natural air convection and not materially affected by reflective and radiant surfaces.
T_C	Case temperature: The temperature measured at a specified location on the case of a device.
V_{CB}	Collector-base voltage: The dc voltage between the collector and the base.
V_{CBO}	Collector-base voltage, base open: The voltage between the collector and base terminals when the emitter terminal is open-circuited.
V_{CEO}	Collector-emitter voltage, base open: The voltage between the collector and the emitter terminals when the base terminal is open-circuited.
V_{EB}	Emitter-base voltage: The dc voltage between the emitter and the base.
V_{EBO}	Emitter-base voltage, collector open: The voltage between the emitter and base terminals with the collector terminal open-circuited.

ELECTRICAL CHARACTERISTICS @ $T_C = +25^\circ\text{C}$
OFF CHARACTERISTICS

Test Conditions	Symbol	Value		Unit
		Min.	Max.	
Collector-Emitter Breakdown Voltage $I_C = -1.0\text{ mA}$, $I_B = 0$, Bias condition D	$V_{(BR)CEO}$	-30	-	V
Collector to Base Cutoff Current $V_{CB} = -20\text{ V}$, $I_E = 0$, Bias condition D $V_{CB} = -30\text{ V}$, Bias condition D	I_{CBO}	-	-100 -100	nA μA
Emitter to Base Cutoff Current $V_{EB} = -3\text{ V}$, Bias condition D	I_{EBO}	-	-100	μA

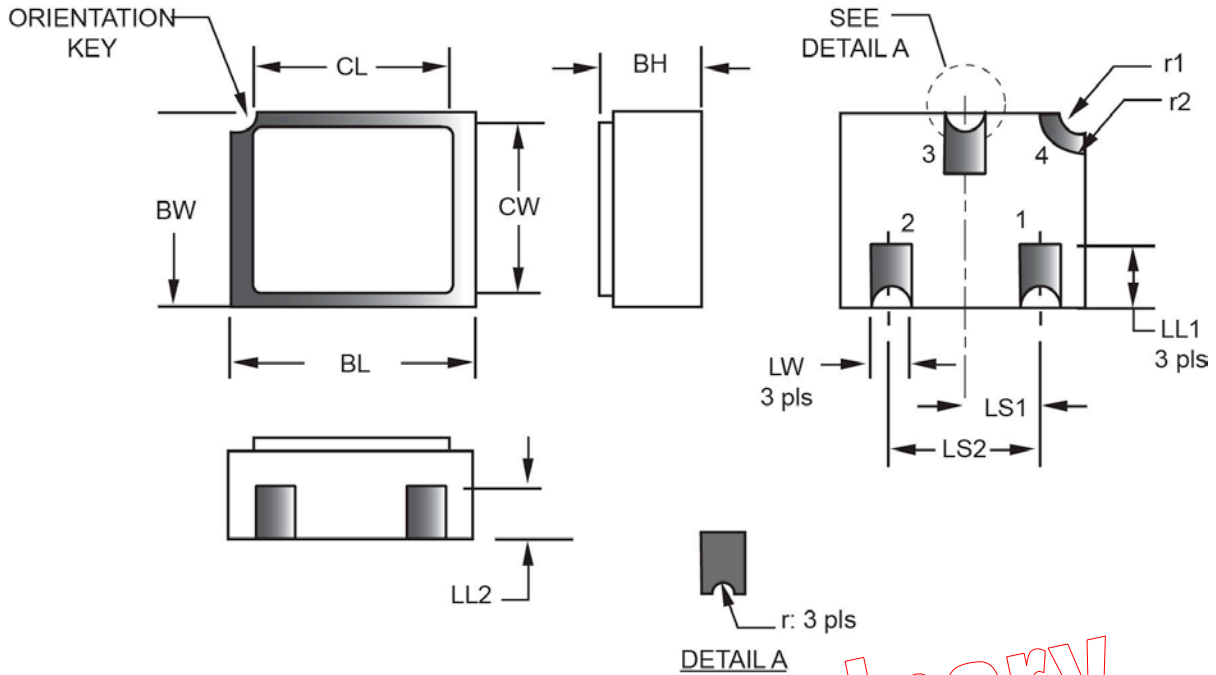
ON CHARACTERISTICS

Test Conditions	Symbol	Value		Unit
		Min.	Max.	
Forward Current transfer ratio $I_C = -0.5\text{ mA}$, $V_{CE} = -10\text{ V}$ $I_C = -2.0\text{ mA}$, $V_{CE} = -10\text{ V}$ $I_C = -5.0\text{ mA}$, $V_{CE} = -10\text{ V}$ $I_C = -5.0\text{ mA}$, $V_{CE} = -10\text{ V}$, $T_A = -55^\circ\text{C}$	h_{FE}	15 20 30 10	165	

DYNAMIC CHARACTERISTICS

Test Conditions	Symbol	Value		Unit
		Min.	Max.	
Magnitude of common emitter small signal short circuit forward current transfer ratio $V_{CE} = -10\text{ V}$, $I_E = -2.0\text{ mA}$, $f = 100\text{ MHz}$	$ h_{fe} $	12	36	
Collector-base time constant $I_E = -2.0\text{ mA}$, $V_{CB} = -10.0\text{ V}$, $f = 63.6\text{ MHz}$	$r_b'C_c$	1.0	8.0	ps
Collector to Base – feedback capacitance $I_E = 0\text{ mA}$, $V_{CB} = -10\text{ V}$, $100\text{ kHz} \leq f \leq 1\text{ MHz}$	C_{cb}		0.8	pF
Noise Figure (50 Ohms) $I_C = -2.0\text{ mA}$, $V_{CE} = -10\text{ V}$, $f = 450\text{ MHz}$, $R_L = 50\ \Omega$	NF		3.5	dB
Small Signal Power Gain (common emitter) $I_C = -2.0\text{ mA}$, $V_{CE} = -10\text{ V}$, $f = 450\text{ MHz}$	G_{pe}	17	25	dB

Preliminary

PACKAGE DIMENSIONS


Preliminary

Symbol	Dimensions				Note	Symbol	Dimensions				Note
	inch		millimeters				inch		millimeters		
	Min	Max	Min	Max			Min	Max	Min	Max	
BH	0.046	0.056	1.17	1.42		LS1	0.036	0.040	0.91	1.02	
BL	0.115	0.128	2.92	3.25		LS2	0.071	0.079	1.80	2.01	
BW	0.085	0.108	2.16	2.74		LW	0.16	0.24	0.41	0.61	
CL	-	0.128	-	3.25		r	-	0.008	-	0.20	
CW	-	0.108	-	2.74		r1	-	0.012	-	0.31	
LL1	0.022	0.038	0.56	0.97		r2	-	0.022	-	0.056	
LL2	0.017	0.035	0.43	0.89							

NOTES:

1. Dimensions are in inches.
2. Millimeters are given for information only.
3. Hatched areas on package denote metallized areas.
4. Pad 1 = Base, Pad 2 = Emitter, Pad 3 = Collector, Pad 4 = Shielding connected to the lid.
5. In accordance with ASME Y14.5M, diameters are equivalent to Φx symbology.